

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: B. Kim et al. Attorney Docket No.: SEMT119849
Application No.: 10/700,782 Art Unit: 1753 / Confirmation No: 5493
Filed: November 3, 2003 Examiner: E. Wong
Title: BATH AND METHOD FOR HIGH RATE COPPER DEPOSITION

RESPONSE TO RESTRICTION REQUIREMENT

Seattle, Washington 98101

March 21, 2007

TO THE COMMISSIONER FOR PATENTS:

REMARKS

Responsive to the restriction requirement mailed February 20, 2007, applicants make the election set forth below, with traverse.

Claims 1-43 are pending in the present application.

The Examiner requires restriction between one of the following six groups.

<u>Group</u>	<u>Claims</u>
I	Claims 1-17, drawn to a plating bath.
II	Claim 18, drawn to a plating bath.
III	Claim 19, drawn to a plating bath.
IV	Claims 20-37, drawn to a process for electroplating copper on a microelectronic workpiece in a through-mask plating application at a rate of 2 micrometers/minute.
V	Claims 38-40, drawn to a process for forming solder bumps on a microelectronic workpiece.
VI	Claims 41-43, drawn to a process for forming a conductive feature employing through-mask plating.

For the following reasons, applicants respectfully traverse the portion of the restriction requirement with respect to the invention of Groups IV and VI.

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